- -- 15. A semiconductor apparatus according to Claim 1, wherein said wiring has a width larger on said inclined portions of said electrically insulating layer than on another portion of said electrically insulating layer.
- 16. A semiconductor apparatus according to Claim 1, further comprising another external connection terminal formed on one of said inclined portions of said electrically insulating layer.
- 17. A semiconductor apparatus according to Claim 1, wherein said electrically insulating layer is covered with another electrically insulating layer.
- 18. A semiconductor apparatus according to Claim 1, wherein:

said electrically insulating layer includes first and second insulating layer members, at least one pair of opposite inclined portions of said first insulating layer member being different in inclination angle from each other, and at least one pair of opposite inclined portions of said second insulating layer member being different in inclination angle from each other; and

said circuit electrode of the semiconductor device is arranged at a central portion of said semiconductor device where said electrically insulating layer is not formed.

